

ABSTRACT OF THE DISCLOSURE

This invention relates to a method of manufacturing an SOI wafer having a low HF defect density using annealing in a reducing atmosphere. An 5 SOI substrate is annealed in a reducing atmosphere at a temperature lower than the melting point of single-crystal silicon. To prevent any HF defects, a holding tool having a surface formed from silicon is used as a holding tool for holding the SOI substrate.

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